

REPLACEMENT CLAIMS

Cancel claim 41.

B<sup>1</sup> 9. (Amended) The semiconductor structure of claim 1 wherein at least one element of the dielectric layer is graded from zero to an amount greater than zero.

B<sup>2</sup> 42. (Amended) A semiconductor structure comprising:  
a semiconductor substrate;  
a dielectric feature comprising titanium, aluminum, nitrogen, and oxygen over the semiconductor substrate.